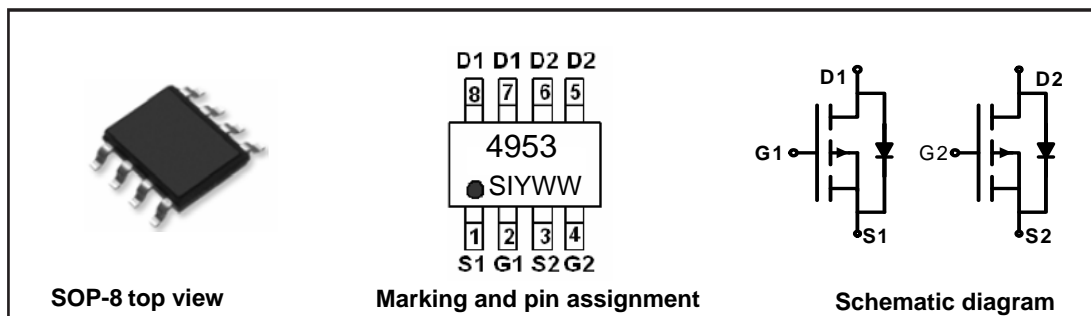


PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Typ
-30V	-5.3A	50 @ V _{GS} = -10V
		70 @ V _{GS} = -4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ^a @ T _J =25°C -Pulsed ^b	I _D	-5.3	A
	I _{DM}	-35	A
Drain-Source Diode Forward Current ^a	I _S	1.7	A
Maximum Power Dissipation ^a	P _D	2	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	62.5	°C/W
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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.6A$		50	65	m-ohm
		$V_{GS}=-4.5V, I_D=-3.6A$		70	85	m-ohm
On-State Drain Current	$I_{D(on)}$	$V_{DS}=-5V, V_{GS}=-10V$	-20			A
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-4.6A$		8		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C_{ISS}	$V_{DS}=-15V, V_{GS}=0V$ $f=1.0MHz$		525		pF
Output Capacitance	C_{OSS}			135		pF
Reverse Transfer Capacitance	C_{RSS}			70		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	$t_{D(on)}$	$V_D=-15V,$ $R_L=15\text{ ohm}$ $I_D=-1A,$ $V_{GEN}=-10V,$ $R_{GEN}=6\text{ ohm}$		7	14	ns
Rise Time	t_r			13	24	ns
Turn-Off Delay Time	$t_{D(off)}$			14	25	ns
Fall Time	t_f			9	17	ns
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-4.6A, V_{GS}=-10V$		6	9	nC
		$V_{DS}=-15V, I_D=-4.6A, V_{GS}=-4.5V$		8.1		nC
Gate-Source Charge	Q_{gs}	$V_{DS}=-15V, I_D=-4.6A,$ $V_{GS}=-10V$		2.2		nC
Gate-Drain Charge	Q_{gd}			2.0		nC

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -1.7A$		-0.8	-1.2	V

Notes

- a. Surface Mounted on FR4 Board, $t_r \leq 10\text{sec}$.
- b. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- c. Guaranteed by design, not subject to production testing.

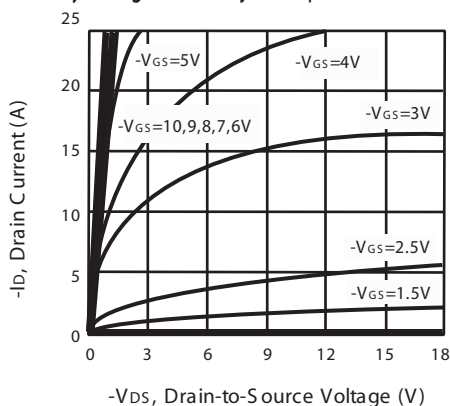


Figure 1. Output Characteristics

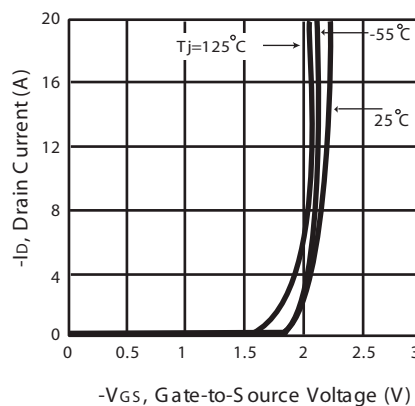


Figure 2. Transfer Characteristics

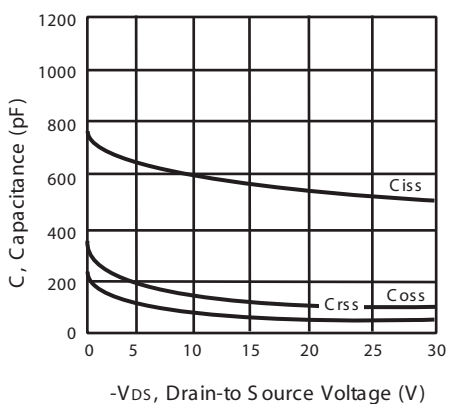


Figure 3. Capacitance

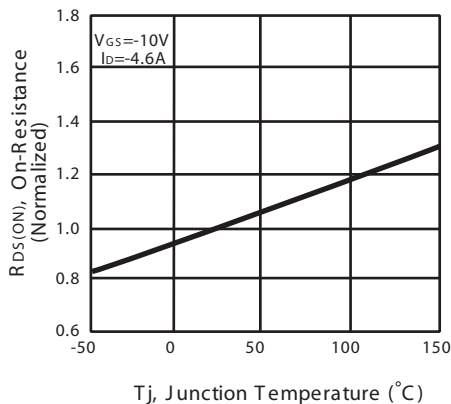


Figure 4. On-Resistance Variation with Temperature

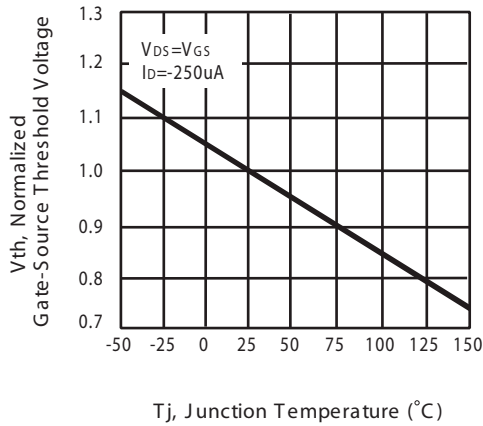


Figure 5. Gate Threshold Variation with Temperature

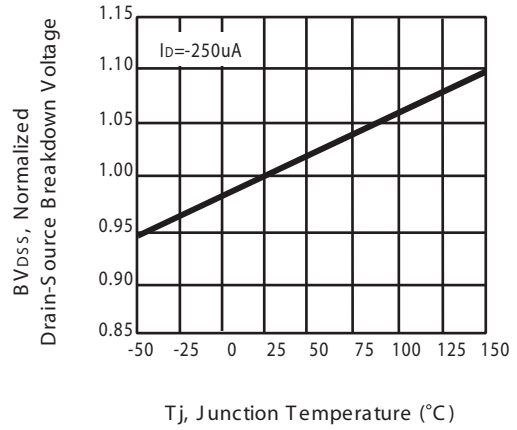


Figure 6. Breakdown Voltage Variation with Temperature

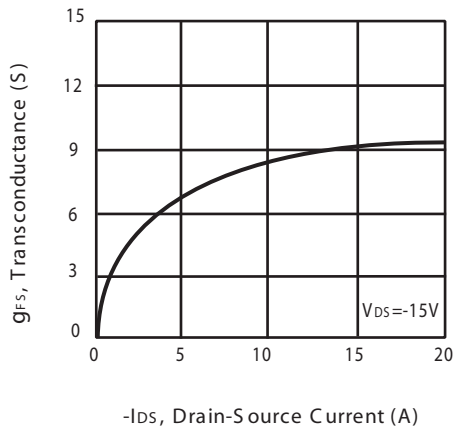


Figure 7. Transconductance Variation with Drain Current

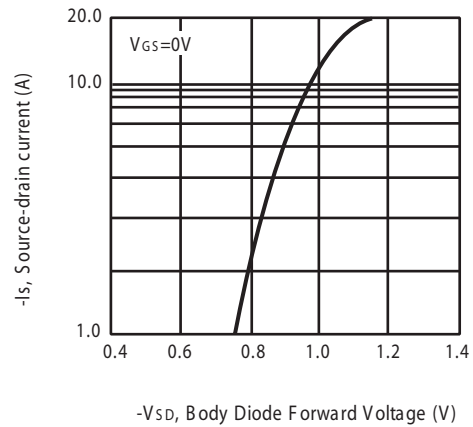


Figure 8. Body Diode Forward Voltage Variation with Source Current

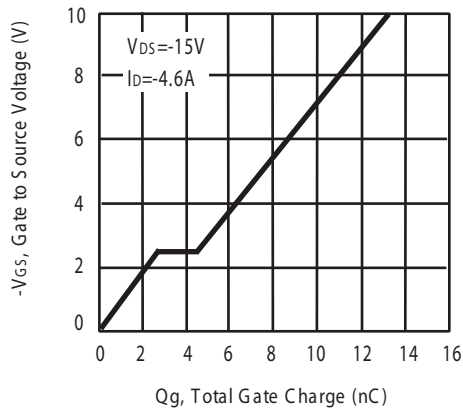


Figure 9. Gate Charge

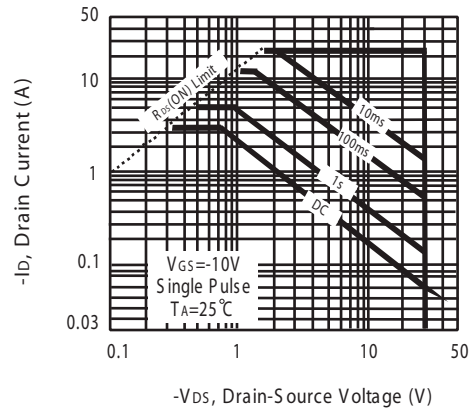


Figure 10. Maximum Safe Operating Area

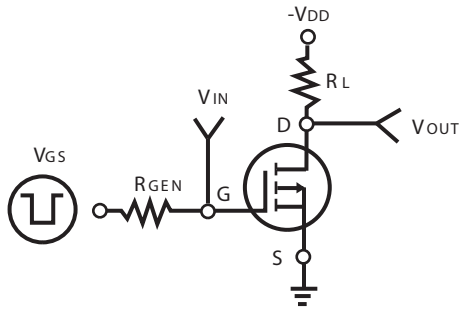


Figure 11. S switching Test Circuit

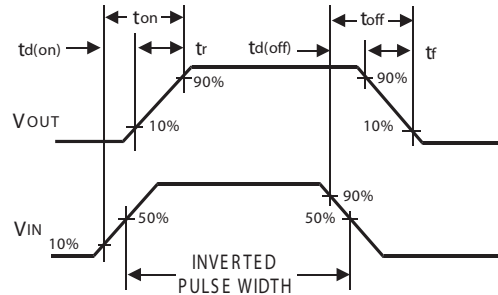


Figure 12. S switching Waveforms

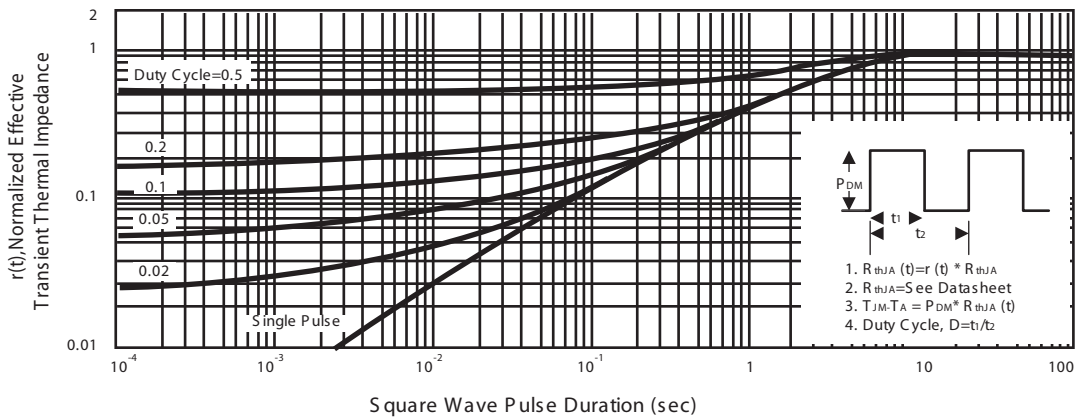
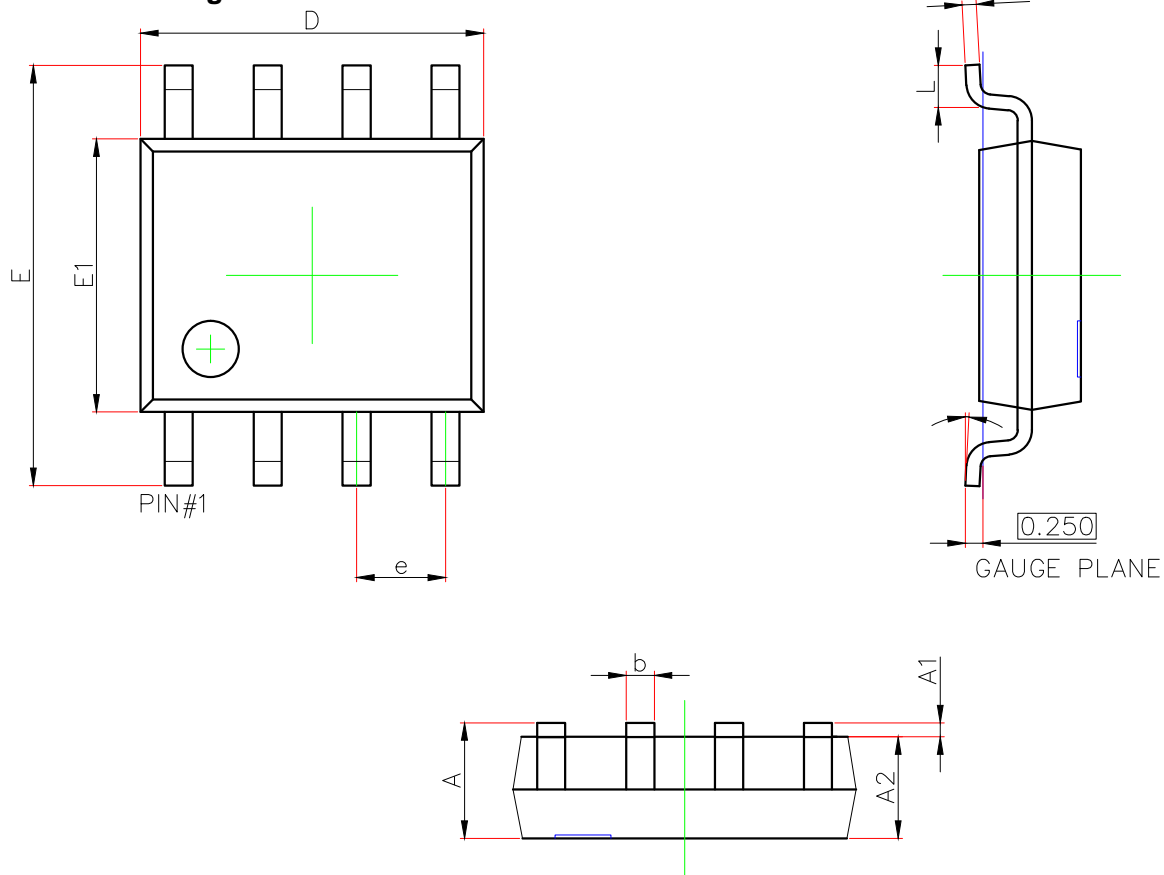


Figure 13. Normalized Thermal Transient Impedance Curve

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°